

IN THE SPECIFICATION

Please replace paragraph [0028], which starts at page 9, line 5 and ends at line 21, with the following.

--A method is disclosed in IEEE Trans. on Electron Devices, Vol. ED-25, No. 10, 1978, p1178- pp. 1178-1185, in which an impurity diffusion layer is formed as an etching stop layer to fabricate an ink-jet nozzle, using the fact that a diffusion layer with an impurity concentration of $7 \times 10^{19}/cm^3$ or more is not etched by an anisotropic etchant. Since the impurity diffusion layer is used as the etching stop layer, if a through-hole is made, cracks are caused by the stress of the etching stop layer when the hole penetrates the substrate. Therefore, it is difficult to use the method described above for making a through-hole. Additionally, at an impurity concentration of $7 \times 10^{19}/cm^3$ or more, the layer is not etched by the etchant. In the present invention, an impurity diffusion layer is used to decrease the side-etching rate, and this effect is achieved even by an impurity concentration of $1 \times 10^{19}/cm^3$ or more.--